

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1 - 11 (canceled)

12. (currently amended) A plasma processing apparatus for processing a product using plasma, comprising:

a power source for applying bias power to an electrode on which a substrate to be processed is disposed;

an insulating layer formed on a surface of said electrode on which said substrate to be processed is disposed;

a first conductive material ~~formed~~ buried within and surrounded by said insulating layer in a ring-like form;

a first feeder line connecting said power source and said first conductive material buried within said insulating layer;

a first variable capacitor provided in said first feeder line;

a silicon ring mounted at a position surrounding the substrate to be processed, on the surface of said electrode on which the substrate to be processed is disposed;

a second conductive material ~~formed~~ buried within and surrounded by said insulating layer and under said silicon ring;

a second feeder line connecting said power source and said second conductive material buried within said insulating layer; and

a second variable capacitor provided in said second feeder line;

wherein one portion of said insulating layer formed on an outer part of said electrode where said first conductive material and said second conductive material are ~~formed~~ buried within and surrounded by said insulating layer has a thickness which is greater than a thickness of another portion of said insulating layer ~~formed on~~ where said first conductive material and said second conductive material are not buried and which extends from a central part of said electrode to the one portion of said insulating layer where said first conductive material and said second conductive material are ~~not formed~~ buried.

13. (previously presented) The apparatus according to claim 12, wherein said insulating layer formed on the surface of said electrode includes alumina.

Claim 14 (canceled)

15. (currently amended) The apparatus according to claim 12, wherein the one portion of said insulating layer is formed on said first conductive material and said second conductive material, between said first conductive material and said electrode, and between said second conductive material and said electrode so as to surround said first conductive material and said second conductive material, and the another portion of said insulating layer is formed at the central part of said electrode where said first conductive material and said second conductive material are not buried.

16. (currently amended) A plasma processing apparatus for processing a product using plasma, comprising:

a high-frequency power source for applying bias power to an electrode on which a substrate to be processed is disposed;

an insulating layer formed on a surface of said electrode on which said substrate to be process is disposed;

a conductive material ~~formed~~ buried within and surrounded by said insulating layer in a ring-like form;

a feeder line connecting said high-frequency power source and said conductive material;

a variable capacitor provided in said feeder line; and

a direct current power source connected between said electrode and said high frequency power source;

wherein one portion of said insulating layer formed on an outer part of said electrode where said conductive material is ~~formed~~ buried within and surrounded by said insulating layer has a thickness which is greater than a thickness of another portion of said insulating layer ~~formed on~~ where said conductive material is not buried and which extends from a central part of said electrode to said one portion or said insulating layer where said conductive material is ~~not formed~~ buried.

17. (previously presented) The apparatus according to claim 16, wherein resonance coils are provided between said feeder line and said electrode and between said direct current power source and said electrode, respectively.

18. (currently amended) The apparatus according to claim 12, wherein said insulating layer at the one portion where said first conductive material is formed has three times the thickness of said another portion of said insulating layer ~~at the central part where said first conductive material and said second conductive material are not~~ formed.

19. (currently amended) The apparatus according to claim 12, wherein said insulating layer at the one portion where said second conductive material is formed has two times the thickness of said another portion of said insulating layer ~~at the central part where said first conductive material and said second conductive material are not~~ formed.

20. (new) The apparatus according to claim 12, wherein said another portion of said insulating layer has a substantially constant thickness.

21. (new) The plasma processing apparatus according to claim 16, wherein said another portion of said insulating layer has a substantially constant thickness.